



## Main Parameters

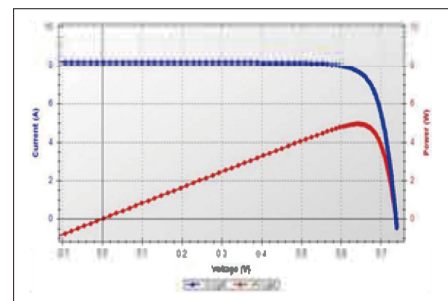
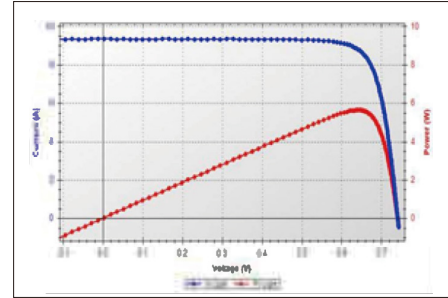
Frontal electrical property distribution

Eff (%)	Pmpp (W)	Uoc (V)	Isc (A)	Umpp (V)	Impp (A)
23.00%	7.59	0.679	13.742	0.579	13.082
22.90%	7.56	0.678	13.714	0.578	13.061
22.80%	7.53	0.677	13.695	0.577	13.046
22.70%	7.49	0.677	13.635	0.577	12.989
22.60%	7.46	0.675	13.617	0.576	12.954
22.50%	7.43	0.673	13.597	0.574	12.941
22.40%	7.40	0.672	13.558	0.573	12.906
22.30%	7.36	0.669	13.558	0.573	12.849
22.20%	7.33	0.668	13.519	0.572	12.814
22.10%	7.30	0.668	13.461	0.572	12.756
22.00%	7.26	0.667	13.436	0.572	12.698
21.90%	7.23	0.667	13.393	0.571	12.662
21.80%	7.20	0.666	13.366	0.569	12.649

## Temp. Coefficient

a	Voltage ( Voc ) : $\sim -0.32\%/^{\circ}\text{C}$
b	Current ( Isc ) : $\sim 0.07\%/^{\circ}\text{C}$
c	Power ( Pm ) : $\sim -0.40\%/^{\circ}\text{C}$

## Characteristic Curve



## Specification

Size	182 mm*182 mm $\pm$ 0.25 mm
Material	P-type mono crystalline silicon
Thickness	170 $\pm$ 30 $\mu$ m
Front (-)	M10 * 0.08mm main grid line (busba silver Ag), 156 secondary grid lines (finger aluminum Al), blue silicon nitride film
Back (+)	M10 * 1.0mm main grid line (busba silver Ag), 180 secondary grid lines (finger aluminum Al), blue silicon nitride film

## Packaging Information

Packaging specification	pcs/case	case/box	pcs/box
	100	16	1600